

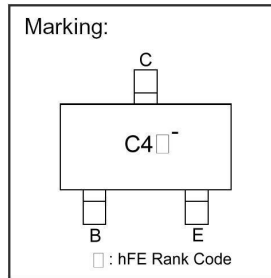
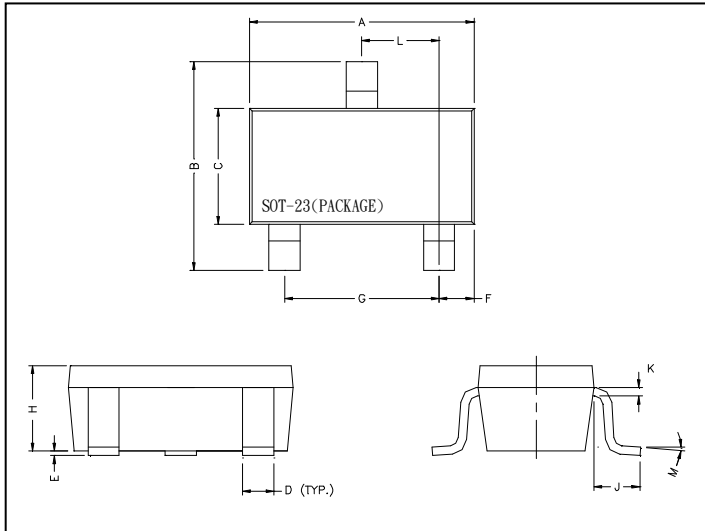
GMBT1815

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT1815 is Designed for use Driver Stage of AF Amplifier and General Purpose Application.

Package Dimensions



REF	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	50	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	150	mA
Total Power Dissipation	PD	250	mW

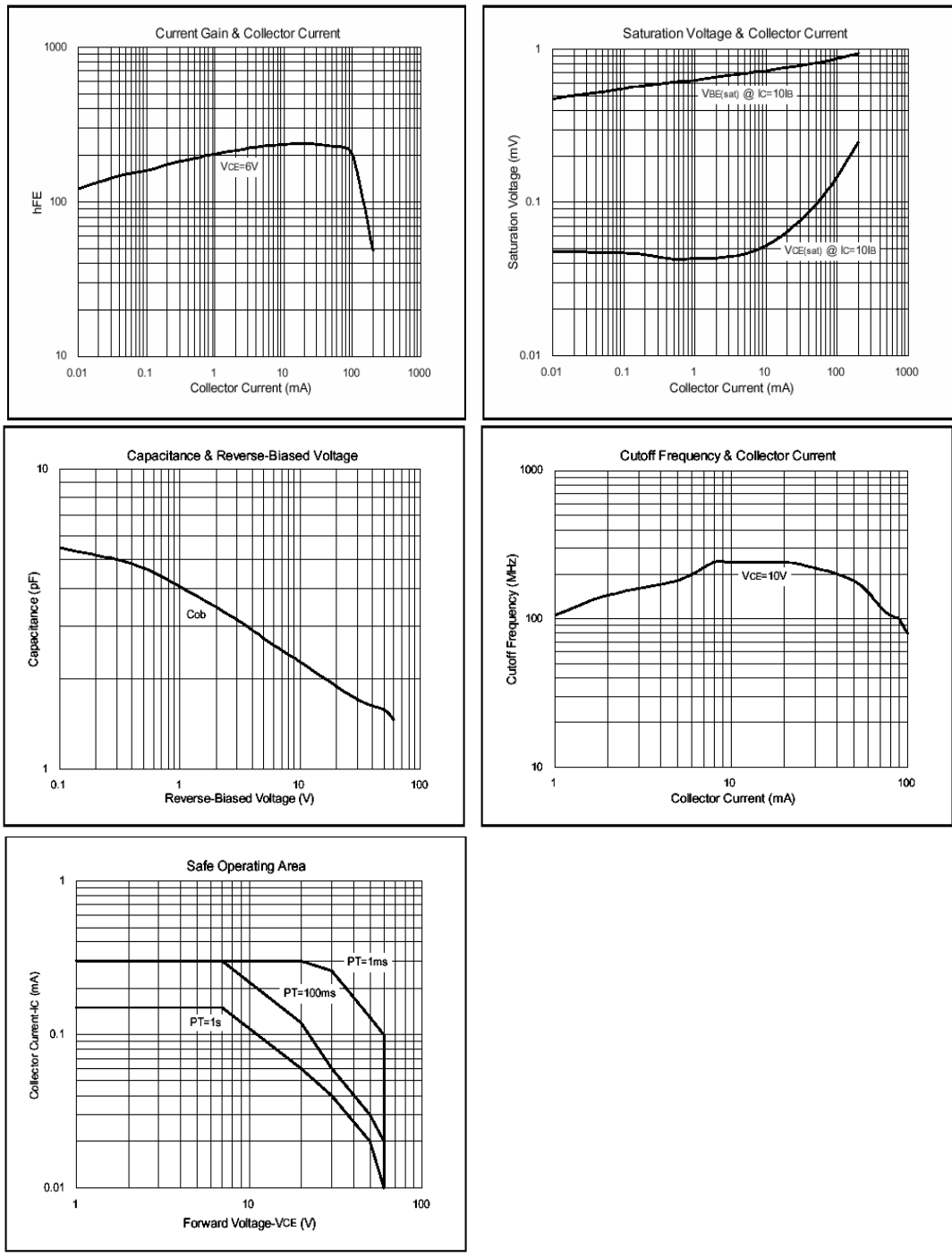
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=100uA
BVCEO	50	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=60V
IEBO	-	-	100	nA	VEB=5V
VCE(sat)	-	-	250	mV	IC=100mA, IB=10mA
VBE(sat)	-	-	1.0	V	IC=100mA, IB=10mA
hFE1	120	-	700		VCE=6V, IC=2mA
hFE2	25	-	-		VCE=6V, IC=150mA
hFE3	80	-	-		VCE=1V, IC=10mA
fT	80	-	-	MHz	VCE=10V, IC=1mA, f=100MHz
Cob	-	-	3.5	pF	VCB=10V, f=1MHz

Classification of hFE1

Rank	C4Y	C4G	C4B
Range	120 - 240	200 - 400	350 - 700

Characteristics Curve



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